

REPLACEMENT CLAIMS

29. (Amended) A semiconductor device comprising:

a substrate; and

an electropolished patterned metal layer provided over said substrate, said electropolished patterned metal layer having a thickness of approximately 50 to 300 Angstroms.

34. (Amended) The semiconductor device of claim 29, wherein said electropolished patterned metal layer has a thickness of approximately 100 Angstroms.

36. (Twice amended) A memory cell comprising:

a conductive layer provided over a semiconductor substrate;

an electropolished patterned metal layer provided over said conductive layer, said electropolished patterned metal layer having a thickness of approximately 50 to 300 Angstroms;

a transistor in electrical communication with said electropolished patterned metal layer, including a gate fabricated on said semiconductor substrate and including a source/drain region in said semiconductor substrate disposed adjacent to said gate; and

a capacitor including an electrode, said electrode being in electrical contact with said source/drain region.

41. (Amended) The memory cell of claim 36, wherein said electropolished patterned metal layer has a thickness of approximately 100 Angstroms.

44. (Amended) A processor-based system comprising:

a processor; and

an integrated circuit coupled to said processor, at least one of said integrated circuit and processor comprising an electropolished patterned metal layer having a thickness of approximately 50 to 300 Angstroms provided over a substrate.

49. The processor-based system of claim 44, wherein said electropolished patterned metal layer has a thickness of approximately 100 Angstroms.